



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **HARADA, Akihiko et al.**

Serial No.: 09/717,143

Filed: November 22, 2000

Group Art Unit: 2826

Examiner: Ahmed Sefer

P.T.O. Confirmation No. 2927

#10/B
1-303
Payton

For: **INSULATED GATE TYPE SEMICONDUCTOR DEVICE AND METHOD FOR
FABRICATING THE SAME**

RESPONSE UNDER 37 CFR §1.116
- EXPEDITED RESPONSE -
GROUP ART UNIT 2826

BOX AF

Commissioner for Patents
Washington, D.C. 20231

December 26, 2002

Sir:

In response to the Office Action dated **July 25, 2002**, please amend the above-identified application as follows:

IN THE CLAIMS:

Please ~~cancel~~ claim 4 without prejudice or disclaimer.

Please ~~amend~~ claims 1, 2, 3 and 5 as indicated below:

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B1
1. (Twice Amended) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, provided with a T-shaped gate electrode comprised of a trunk-shaped main gate electrode extending in parallel with respect to said semiconductor substrate, and a crosspiece-shaped conductor pattern extending in parallel with respect to said semiconductor substrate and also extending toward the width direction of said main gate electrode and having a